



<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	<b>Atty Docket No.</b>	NOVLP097/NVLS-2906
	<b>Application No.:</b>	10/807,680
	<b>Applicant</b>	Wu et al.
	<b>Filing Date</b>	March 23, 2004
	<b>Group</b>	1792
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### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
/M.L.P./	1.	7,208,389 B1	04.24.07	Tipton et al.	X	X	
	2.	7,253,125 B1	08.07.07	Bandyopadhyay et al.			
	3.	7,265,061	09.04.07	Cho et al.			
	4.	7,018,918	03.2006	Kloster et al.			
	5.	2006/0024976	02.2006	Waldfried et al.			
	6.	2007/0281497	12.2007	Liu et al.			
	7.	6,136,680	10.2000	Lai et al.			
	8.	2005/0156285 A1	07.2005	Gates et al.			
	9.	7,064,088 B2	06.2006	Hyodo et al.			
	10.	7,241,704 B1	07.10.07	Wu et al.			
/M.L.P./	11.	7,176,144	02.13.07	Wang et al.			

### Foreign Patent or Published Foreign Patent Application

Examiner Initial	Document No.	Publication Date	Country or Patent Office	Class	Sub-Class	Translation	
						Yes	No
/M.L.P./	12.	01-107519	25.04.1989	Japan		X	

English abstract

### Other Documents

Examiner Initial	No.	Author, Title, Place (e.g. Journal) of Publication, Date
	13.	Schravendijk, et al., "UV Treatment of STI Films for Stress," Novellus Systems, Inc., Application No. 11/811,048, filed June 7, 2007. [NOVLP192/NVLS-3219]
/M.L.P./	14.	Arghavani et al., <i>Strain Engineering in Non-Volatile Memories</i> , Reed Business Information, 2007, six pages. no month
	15.	Notice of Allowance and Fee Due mailed May 22, 2006, from U.S. Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-2020].
	16.	Allowed Claims from U.S. Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-2020].
	17.	Notice of Allowance and Fee Due mailed April 4, 2007, from U.S. Application No. 10/825,888 [Atty Dkt No. NOVLP088/NVLS-2882].
	18.	Allowed Claims from U.S. Application No. 10/825,888 [Atty Dkt No. NOVLP088/NVLS-2882].

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	19.	Bandyopadhyay et al., "Method to Improve Mechanical Strength of Low-K Dielectric Film Using Modulated UV Exposure," Novellus Systems, Inc., Application No. 11/824,049, filed June 28, 2007 [NOVLP088C1/NVLS-2882C1]
	20.	Notice of Allowance and Fee Due mailed October 10, 2006, from U.S. Application No. 10/800,377 [Atty Dkt No. NOVLP089/NVLS-2886/2887]
	21.	Allowed Claims from U.S. Application No. 10/800,377 [Atty Dkt No. NOVLP089/NVLS-2886/2887]
	22.	Allowed Claims from U.S. Application No. 10/860,340 [Atty Dkt No. NOVLP099/NVLS-2896]
	23.	U.S. Office Action mailed December 12, 2007, from U.S. Application No. 11/146,456 [Atty Dkt No. NOVLP100X1/NVLS-3040]
	24.	U.S. Office Action mailed October 3, 2007, from U.S. Application No. 11/115,576 [Atty Dkt No. NOVLP127/NVLS-3044]
	25.	Shaviv et al., "UV Treatment to Improve Integrity and Performance of Front End Dielectrics," Novellus Systems, Inc., Application No. 11/622,409, filed January 11, 2007. [NOVLP188/NVLS-3213]
	26.	van Schravendijk et al., "UV Treatment for Carbon-Containing Low-K Dielectric Repair in Semiconductor Processing," Novellus Systems, Inc., Application No. 11/590,661, filed October 30, 2006. [NOVLP190/NVLS-3216]
	27.	Shrinivassan et al., "Multi-Station Sequential Curing of Dielectric Films," Novellus Systems, Inc., Application No. 11/688,695, filed March 20, 2007. [NOVLP197/NVLS-3262]
	28.	Varadarajan et al., "A Cascaded Cure Approach to Fabricate Highly Tensile Silicon Nitride Films," Novellus Systems, Inc., Application No. 11/897,838, filed August 31, 2007. [NOVLP236/NVLS-3332]
	29.	Van den Hoek, et al., "VLSI Fabrication Processes for Introducing Pores Into Dielectric Materials," Novellus Systems, Inc., Application No. 11/606,340, filed November 28, 2006. [NOVLP100C1/NVLS-2956C1]
	30.	U.S. Office Action mailed January 10, 2008, from U.S. Application No. 11/622,423 [Atty Dkt No. NOVLP189/NVLS-3213]
M.L.P./	31.	Bhadri Varadarajan et al., "Development of High Stress SiN Films for Use with Strained Silicon Technologies"; Proc. 68 <sup>th</sup> Symp. On Semiconductors and IC Tech.; Kyoto 2005. no month
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	33.	Allowed Claims from U.S. Application No. 10/800,409. [NOVLP098/NVLS-2907]
	34.	U.S. Office Action mailed October 4, 2007, from U.S. Application No. 10/820,525 [Atty Dkt No. NOVLP091/NVLS-2889]
	35.	Wu et al., "Methods For Producing Low Stress Porous Low-K Dielectric Materials Using Precursors With Organic Functional Groups", U.S. Application No. 11/764,750, filed June 18, 2007 [Atty Dkt: NOVLP106D1/NVLS-2930D1]

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	36.	U.S. Office Action mailed October 29, 2007, from U.S. Application No. 11/764,750 [Atty Dkt No. NOVLP106D1/NVLS-2930D1].
	37.	Wu et al., "Methods For Producing Low-K CDO Films," U.S. Application No. 11/936,754, filed November 7, 2007 [Atty Docket No.: NOVLP098D1/NVLS-2907D1]
	38.	Wu et al., "Methods For Improving Integration Performance of Low Stress CDO Films", U.S. Application No. 11/936,752, filed November 7, 2007 [Atty Dkt. NOVLP107D1/NVLS-2932D1]
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	41.	U.S. Office Action mailed July 12, 2006, from U.S. Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-2821].
	42.	U.S. Office Action mailed August 14, 2007, from U.S. Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS-2794].
	43.	U.S. Office Action mailed February 2, 2007, from U.S. Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000621].
	44.	Willibrordus Gerardus Maria van den Hoek et al., "VLSI Fabrication Processes for Introducing Pores Into Dielectric Materials," U.S. Application No. 11/606,340, Filed November 28, 2006 (Atty Dkt: NOVLP100C1/NVLS-2956C1)
/M.L.P./	45.	Cabarrocas et al., "Plasma production of nanocrystalline silicon particles and polymorphous silicon thin films for large-area electronic devices," Pure Appl. Chem., Vol. 74, No. 3, pp. 359-367, 2002. no month
	46.	Kim et al., "Particle formation during low-pressure chemical vapor deposition from silane and oxygen: Measurement, modeling, and film properties," J. Vac. Sci. Technol. A 20(2), Mar/Apr 2002, pp. 413-423.
	47.	Suh et al., "Modeling particle formation during low-pressure silane oxidation: Detailed chemical kinetics and aerosol dynamics," J. Vac. Sci. Technol. A 19(3), May/Jun 2001, pp. 940-951.
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	49.	Girshick et al., "Numerical Modeling of Gas-Phase Nucleation and Particle Growth during Chemical Vapor Deposition of Silicon," Journal of The Electrochemical Society, 147 (6) 2303-2311 (2000). no month
/M.L.P./	50.	Fonzo, et al., "Focused nanoparticle-beam deposition of patterned microstructures," Applied Physics Letters, Volume 77, Number 6, August 7, 2000, pages 910-912.
	51.	Notice of Allowance mailed May 22, 2006, from U.S. Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-2820].
	52.	Allowed Claims from U.S. Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-2820]
	53.	Notice of Allowance mailed October 3, 2006, from U.S. Application No. 10/785,235 [Atty Dkt No. NOVLP083/NVLS-2873].
	54.	Allowed Claims from U.S. Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875]

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	<del>55.</del>	<del>U.S. Office Action mailed December 12, 2007, from U.S. Application No. 11/146,456 [Atty Dkt No. NOVLP100X1/NVLS-3040].</del>
/MLP/	56.	Qingguo W and Karne K. Gleason, "Pulsed Plasma CVD of OSG and OSG/Organic Copolymer Films", June 2002, <u>no publication source given</u>
/MLP/	57.	Richard J. Lewis, Sr, Hawley's 'Condensed Chemical Dictionary, 12 <sup>th</sup> Edition, Copyright 1993, pp. 917-918 and 1124 <u>no month</u>

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